

AMENDMENTS TO THE CLAIMS

Please amend the claims as follows:

1 – 12. (Canceled)

13. (Currently Amended) A method of fabricating a semiconductor device including a hole pattern, comprising the steps of:

employing linearly polarized light to transfer on a resist film formed on a wafer a mask pattern formed on a mask;

patterning said resist film; and

employing said resist film patterned to form a pattern, wherein to form said hole pattern said mask pattern has an opening larger in width in a first direction parallel to said linearly polarized light's direction of polarization than a second direction orthogonal to said first direction,

wherein said mask pattern has a halftone region.

14 – 17. (Canceled)